Dual General Purpose Transistors

NPN/PNP Dual (Complementary)

This transistor is designed for general purpose amplifier applications. It is housed in the SOT–563 which is designed for low power surface mount applications.

Features

- Lead–Free Solder Plating
- Low V_{CE(SAT)}, <0.5 V
- These are Pb–Free Devices

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--------------------------------|------------------|-------|------|
| Collector – Emitter Voltage | V _{CEO} | -60 | V |
| Collector-Base Voltage | V _{CBO} | -50 | V |
| Emitter-Base Voltage | V _{EBO} | -6.0 | V |
| Collector Current – Continuous | Ι _C | -100 | mAdc |

THERMAL CHARACTERISTICS

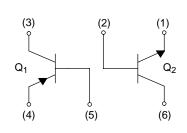
| Characteristic (One Junction Heated) | Symbol | Мах | Unit |
|---|-----------------------------------|------------------------------|-------------|
| Total Device Dissipation T _A = 25°C Derate above 25°C | P _D | 357 (Note 1) 2.9 (Note 1) | mW mW/°C |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta J A}$ | 350 (Note 1) | °C/W |
| Characteristic (Both Junctions Heated) | Symbol | Max | Unit |
| Total Device Dissipation $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$ | P _D | 500 (Note 1) 4.0 (Note 1) | mW mW/°C |
| Thermal Resistance, Junction-to-Ambient | R_{\thetaJA} | 250 (Note 1) | °C/W |
| Junction and Storage Temperature Range | T _J , T _{stg} | -55 to +150 | °C |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability. 1. FR-4 @ Minimum Pad.



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MARKING DIAGRAM



3Z = Specific Device Code M = Month Code = Pb-Free Package to: Migradet may be in either leasting

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$)

| Characteristic | Symbol | Min | Тур | Мах | Unit |
|--|----------------------|------|-----|------|------|
| Q1: PNP | | - | - | - | |
| Collector–Base Breakdown Voltage ($I_C = -50 \mu Adc, I_E = 0$) | V _{(BR)CBO} | -60 | - | - | Vdc |
| Collector–Emitter Breakdown Voltage ($I_C = -1.0 \text{ mAdc}, I_B = 0$) | V _{(BR)CEO} | -50 | - | - | Vdc |
| Emitter–Base Breakdown Voltage (I _E = –50 μAdc, I _E = 0) | V _{(BR)EBO} | -6.0 | - | - | Vdc |
| Collector–Base Cutoff Current ($V_{CB} = -30$ Vdc, $I_E = 0$) | I _{CBO} | - | - | -0.5 | nA |
| Emitter–Base Cutoff Current (V _{EB} = -5.0 Vdc, I _B = 0) | I _{EBO} | - | - | -0.5 | μΑ |
| Collector–Emitter Saturation Voltage (Note 2) ($I_C = -50 \text{ mAdc}, I_B = -5.0 \text{ mAdc}$) | V _{CE(sat)} | _ | - | -0.5 | Vdc |
| DC Current Gain (Note 2) ($V_{CE} = -6.0$ Vdc, $I_C = -1.0$ mAdc) | h _{FE} | 120 | - | 560 | - |
| Transition Frequency ($V_{CE} = -12 \text{ Vdc}, I_C = -2.0 \text{ mAdc}, f = 30 \text{ MHz}$) | f _T | _ | 140 | _ | MHz |
| Output Capacitance (V _{CB} = -12 Vdc, I _E = 0 Adc, f = 1 MHz) | C _{OB} | - | 3.5 | - | pF |
| Q2: NPN | | | | | |
| Collector-Base Breakdown Voltage $(I_C = 50 \ \mu Adc, I_E = 0)$ | V _{(BR)CBO} | 60 | - | - | Vdc |
| Collector-Emitter Breakdown Voltage ($I_C = 1.0 \text{ mAdc}, I_B = 0$) | V _{(BR)CEO} | 50 | - | - | Vdc |
| Emitter-Base Breakdown Voltage (I _E = 50 μAdc, I _E = 0) | V _{(BR)EBO} | 7.0 | - | - | Vdc |
| Collector-Base Cutoff Current ($V_{CB} = 60 \text{ Vdc}, I_E = 0$) | I _{CBO} | _ | - | 0.5 | μΑ |
| Emitter-Base Cutoff Current ($V_{EB} = 7.0 \text{ Vdc}, I_B = 0$) | I _{EBO} | - | - | 0.5 | μΑ |
| Collector-Emitter Saturation Voltage (Note 3) ($I_C = 50$ mAdc, $I_B = 5.0$ mAdc) | V _{CE(sat)} | _ | _ | 0.4 | Vdc |
| DC Current Gain (Note 3) (V _{CE} = 6.0 Vdc, I _C = 1.0 mAdc) | h _{FE} | 120 | _ | 560 | - |
| Transition Frequency (V _{CE} = 12 Vdc, I _C = 2.0 mAdc, f = 30 MHz) | f _T | _ | 180 | - | MHz |
| Output Capacitance (V _{CB} = 12 Vdc, I _C = 0 Adc, f = 1 MHz) | C _{OB} | _ | 2.0 | - | pF |

2. Pulse Test: Pulse Width \leq 300 μ s, D.C. \leq 2%.

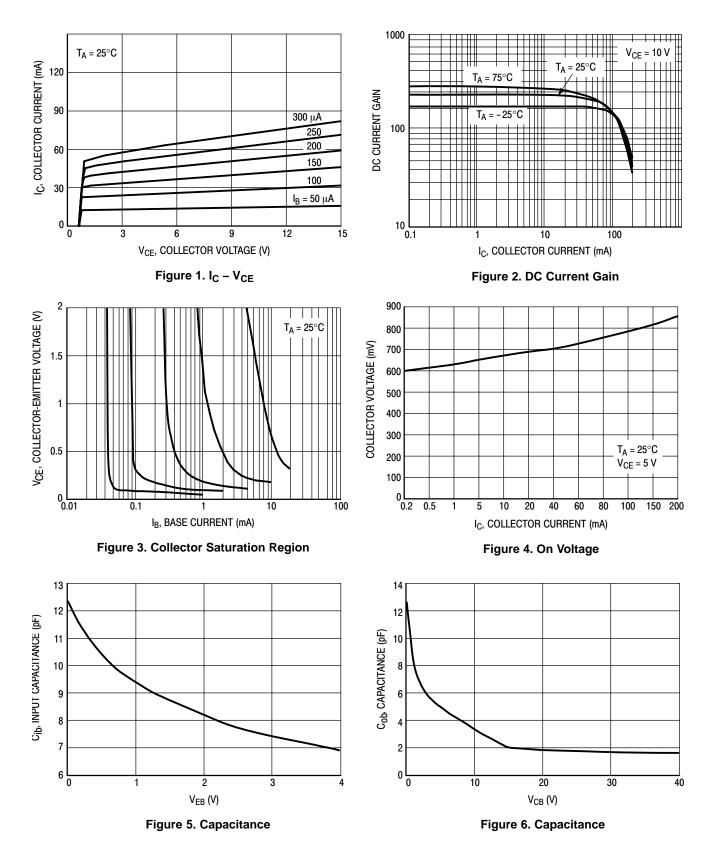
3. Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.

ORDERING INFORMATION

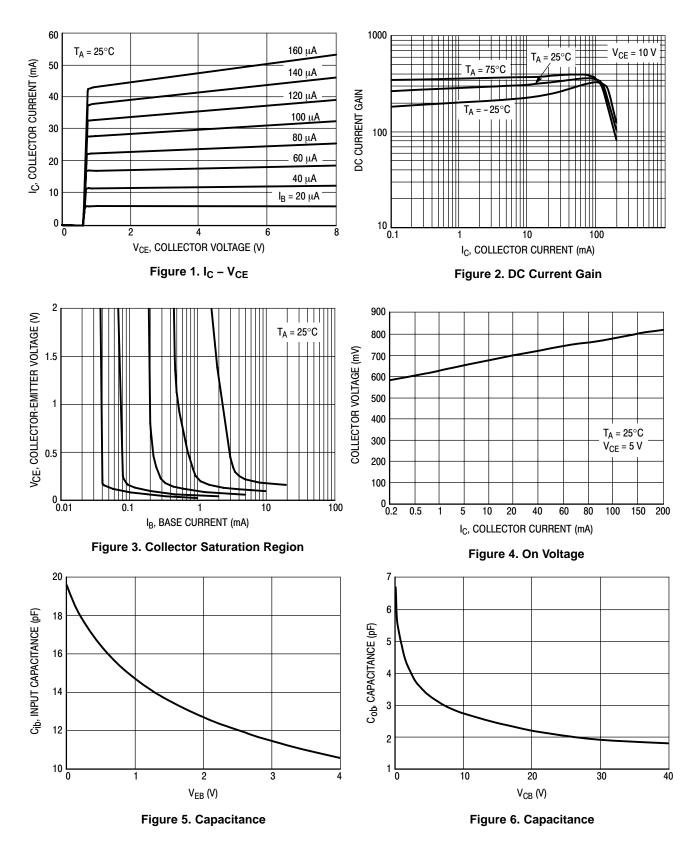
| Device | Package Shipping [†] | |
|-------------|-------------------------------|--------------------------|
| EMZ1DXV6T1 | SOT-563* | 4000 Units / Tape & Reel |
| EMZ1DXV6T1G | SOT-563* | 4000 Units / Tape & Reel |
| EMZ1DXV6T5 | SOT-563* | 8000 Units / Tape & Reel |
| EMZ1DXV6T5G | SOT-563* | 8000 Units / Tape & Reel |

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*This package is inherently Pb-Free.

TYPICAL ELECTRICAL CHARACTERISTICS – Q1, PNP

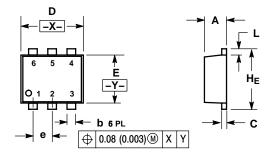


TYPICAL ELECTRICAL CHARACTERISTICS – Q2, NPN



PACKAGE DIMENSIONS

SOT-563, 6 LEAD CASE 463A-01 ISSUE F



NOTES

- 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETERS 2.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

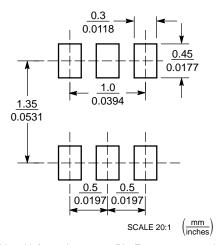
| | MILLIMETERS INCHES | | | 3 | | |
|-----|--------------------|------|------|----------|-------|-------|
| DIM | MIN | NOM | MAX | MIN | NOM | MAX |
| Α | 0.50 | 0.55 | 0.60 | 0.020 | 0.021 | 0.023 |
| b | 0.17 | 0.22 | 0.27 | 0.007 | 0.009 | 0.011 |
| С | 0.08 | 0.12 | 0.18 | 0.003 | 0.005 | 0.007 |
| D | 1.50 | 1.60 | 1.70 | 0.059 | 0.062 | 0.066 |
| E | 1.10 | 1.20 | 1.30 | 0.043 | 0.047 | 0.051 |
| е | 0.5 BSC | | | 0.02 BSC | | |
| L | 0.10 | 0.20 | 0.30 | 0.004 | 0.008 | 0.012 |
| HE | 1.50 | 1.60 | 1.70 | 0.059 | 0.062 | 0.066 |

STYLE 1: PIN 1. EMITTER 1

BASE 1 COLLECTOR 2 2. 3. 4. EMITTER 2

BASE 2 5. 6. COLLECTOR 1

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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